

<b>Notice of References Cited</b>	Application/Control No. 09/905,090	Applicant(s)/Patent Under Reexamination LESCOT ET AL.	
	Examiner Hugh Jones	Art Unit 2128	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US- 6,291,324	9/2001	<del>LESCOT</del> Lescot et al.	438/510
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Shin et al.; MOSFET drain engineering analysis for deep-submicrometer dimensions: a new approach; IEEE Trans. Elect. Dev.; pp. 1922-1927; 8/1992.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.